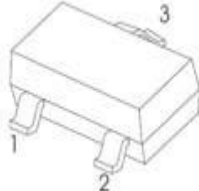
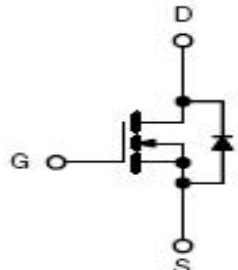
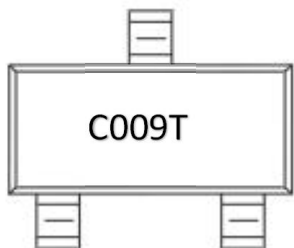
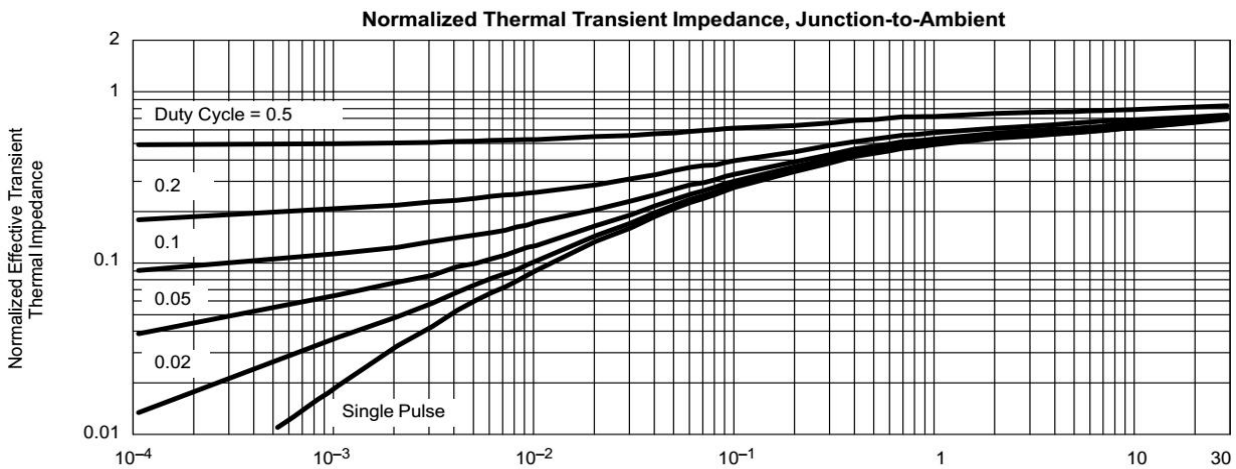
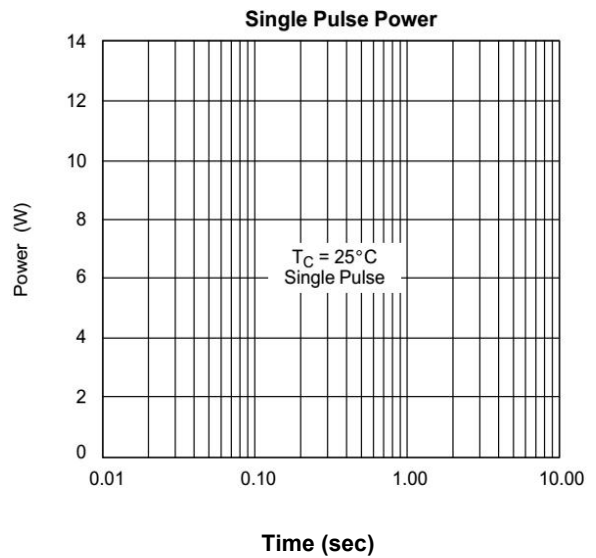
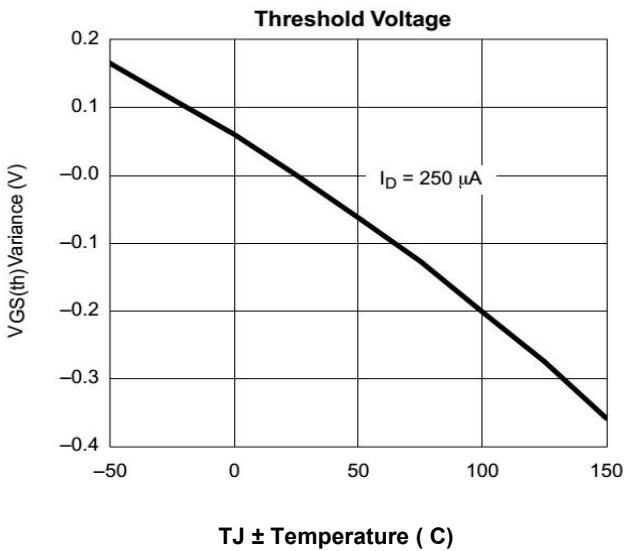
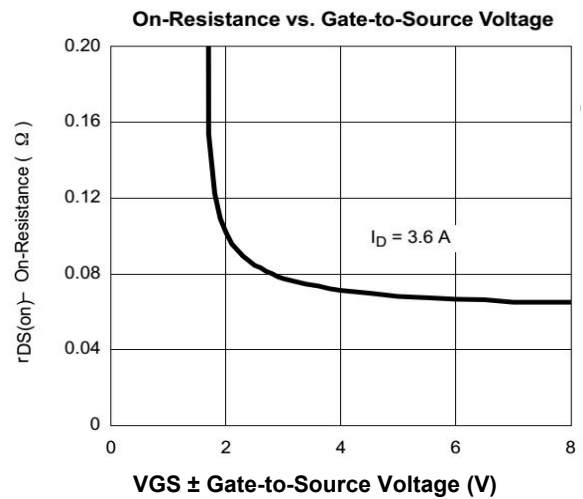
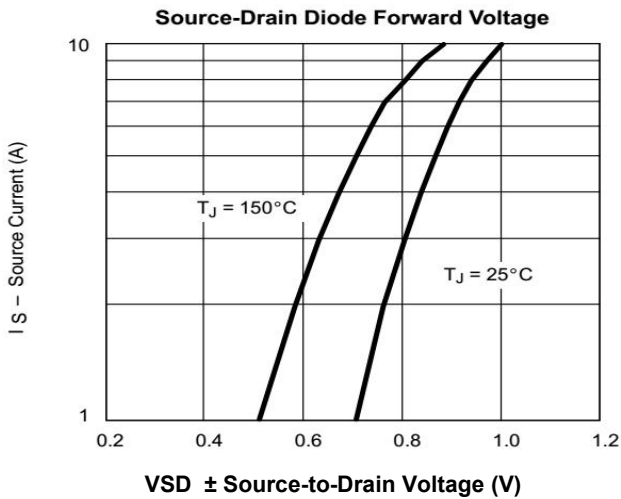


N-Channel 20-V(D-S) MOSFET		SOT-23 Plastic-Encapsulate MOSFETS	
<p style="text-align: center;"><u>SOT-23</u></p>  <p>1.GATE 2.SOURCE 3.DRAIN</p> <p style="text-align: center;">Equivalent Circuit</p> 		<p>Features</p> <ul style="list-style-type: none"> ※ TrenchFET Power MOSFET <p>Application</p> <ul style="list-style-type: none"> ※ Load Switch for Portable Devices ※ DC/DC Converter <p>MARKING</p> 	
V(BR)DSS	RDS(on)MAX		ID
20 V	25mΩ @4.5V		6A
	34.5mΩ @2.5V		
Maximum ratings (Ta=25°C unless otherwise noted)			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	20	V
Gate-Source Voltage	VGS	±12	
Continuous Drain Current	ID	6	A
Continuous Source-Drain Current (Diode Conduction)	IS	0.6	
Power Dissipation	PD		W
Thermal Resistance from Junction to Ambient (t≤5s)	RθJA	312.5	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	°C

MOSFET ELECTRICAL CHARACTERISTICS						
Electrical Characteristics Ta = 25 °C						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID =10μA	20			V
Gate-threshold voltage	VGS(th)	VDS =VGS, ID =250μA	0.40		1	V
Gate-body leakage	IGSS	VDS =0V, VGS =±12V			±100	nA
Zero gate voltage drain current	IDSS	VDS =20V, VGS =0V			1	μA
Drain-source on-resistance ^a	RDS(on)	VGS =4.5V, ID = 6A		0.021	0.025	Ω
		VGS =2.5V, ID =5.2A		0.028	0.034	Ω
Forward transconductance ^a	gfs	VDS =5V, ID =3.6A		8		S
Diode forward voltage	VSD	IS=0.94A, VGS=0V		0.74	1.2	V
Dynamic						
Total gate charge	Qg	VDS =10V, VGS =4.5V, ID =3.6A		7.7	10	nC
Gate-source charge	Qgs			0.32		nC
Gate-drain charge	Qgd			2.1		nC
Input capacitance ^b	Ciss	VDS =10V, VGS =0V, f=1MHz		574		pF
Output capacitance ^b	Coss			70		pF
Reverse transfer capacitance ^b	Crss			60		pF
Switching^b						
Turn-on delay time	td(on)	VDD=10V		78.7		ns
Rise time	tr	RL=5.5Ω, ID ≈3.6A,		128		ns
Turn-off delay time	td(off)	VGEN=4.5V, Rg=6Ω		453		ns
Fall time	tf			80.9		ns
<p>Note :</p> <ol style="list-style-type: none"> 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. Surface Mounted on FR4 Board, t < 5 sec. 3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%. 4. Guaranteed by design, not subject to production testing. 						

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)